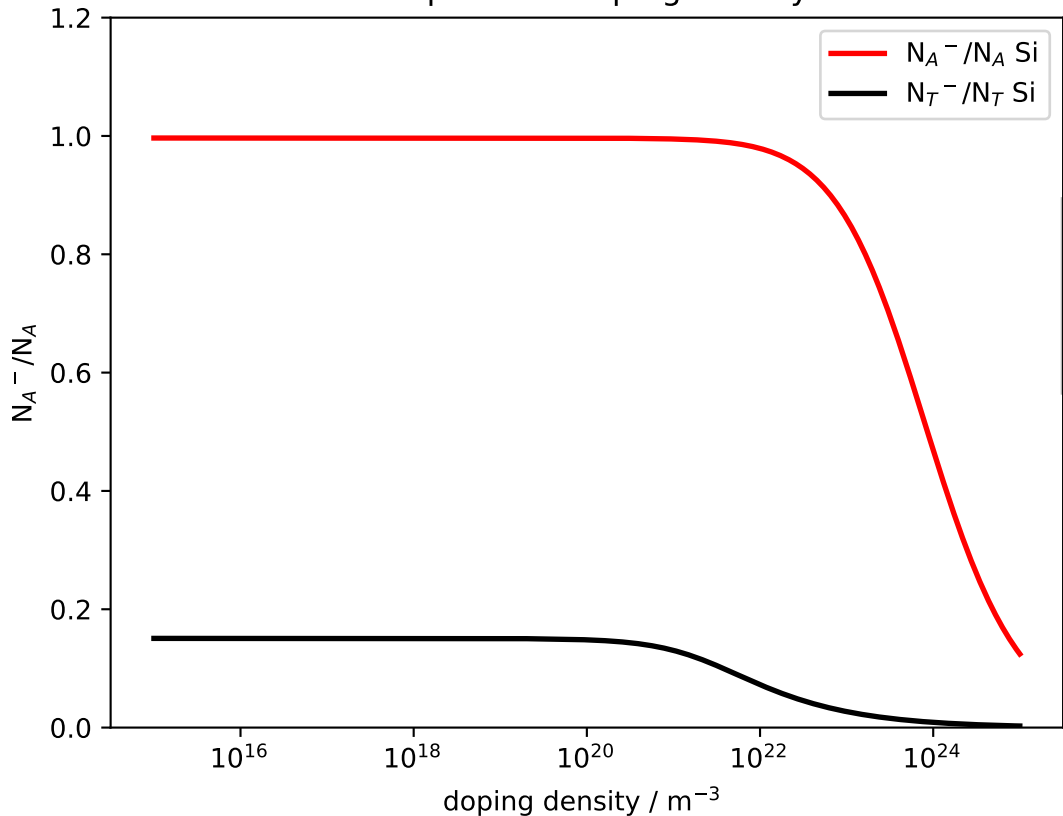


Number of Ionized Dopants vs doping density for Si at $T = 300\text{K}$



Si Param

$$E_g = 1.1$$

$$m_n^* = 1.1$$

$$m_p^* = 0.5$$